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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	ARM® Cortex®-M3
Core Size	32-Bit Single-Core
Speed	120MHz
Connectivity	CANbus, Ethernet, I²C, IrDA, LINbus, Memory Card, SPI, UART/USART, USB OTG
Peripherals	Brown-out Detect/Reset, DMA, I²S, LCD, POR, PWM, WDT
Number of I/O	82
Program Memory Size	768KB (768K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	132K x 8
Voltage - Supply (Vcc/Vdd)	1.8V ~ 3.6V
Data Converters	A/D 16x12b; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	100-LQFP
Supplier Device Package	100-LQFP (14x14)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32f207vft6

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Table 6. USART feature comparison

USART name	Standard features	Modem (RTS/CTS)	LIN	SPI master	irDA	Smartcard (ISO 7816)	Max. baud rate in Mbit/s (oversampling by 16)	Max. baud rate in Mbit/s (oversampling by 8)	APB mapping
USART1	X	X	X	X	X	X	1.87	7.5	APB2 (max. 60 MHz)
USART2	X	X	X	X	X	X	1.87	3.75	APB1 (max. 30 MHz)
USART3	X	X	X	X	X	X	1.87	3.75	APB1 (max. 30 MHz)
UART4	X	-	X	-	X	-	1.87	3.75	APB1 (max. 30 MHz)
UART5	X	-	X	-	X	-	3.75	3.75	APB1 (max. 30 MHz)
USART6	X	X	X	X	X	X	3.75	7.5	APB2 (max. 60 MHz)

3.23 Serial peripheral interface (SPI)

The STM32F20x devices feature up to three SPIs in slave and master modes in full-duplex and simplex communication modes. SPI1 can communicate at up to 30 Mbits/s, while SPI2 and SPI3 can communicate at up to 15 Mbit/s. The 3-bit prescaler gives 8 master mode frequencies and the frame is configurable to 8 bits or 16 bits. The hardware CRC generation/verification supports basic SD Card/MMC modes. All SPIs can be served by the DMA controller.

The SPI interface can be configured to operate in TI mode for communications in master mode and slave mode.

3.24 Inter-integrated sound (I^2S)

Two standard I^2S interfaces (multiplexed with SPI2 and SPI3) are available. They can operate in master or slave mode, in half-duplex communication modes, and can be configured to operate with a 16-/32-bit resolution as input or output channels. Audio sampling frequencies from 8 kHz up to 192 kHz are supported. When either or both of the I^2S interfaces is/are configured in master mode, the master clock can be output to the external DAC/CODEC at 256 times the sampling frequency.

All I2Sx interfaces can be served by the DMA controller.

3.25 SDIO

An SD/SDIO/MMC host interface is available, that supports MultiMediaCard System Specification Version 4.2 in three different databus modes: 1-bit (default), 4-bit and 8-bit.

Table 8. STM32F20x pin and ball definitions (continued)

Pins						Pin name (function after reset)(1)	Pin type	I/O structure	Note	Alternate functions	Additional functions
LQFP64	WLCSP64+2	LQFP100	LQFP144	LQFP176	UFBGA176						
-	-	-	14	20	J3	PF4	I/O	FT	(4)	FSMC_A4, EVENTOUT	ADC3_IN14
-	-	-	15	21	K3	PF5	I/O	FT	(4)	FSMC_A5, EVENTOUT	ADC3_IN15
-	H9	10	16	22	G2	V_{SS}	S	-	-	-	-
-	-	11	17	23	G3	V_{DD}	S	-	-	-	-
-	-	-	18	24	K2	PF6	I/O	FT	(4)	TIM10_CH1, FSMC_NIORD, EVENTOUT	ADC3_IN4
-	-	-	19	25	K1	PF7	I/O	FT	(4)	TIM11_CH1,FSMC_NREG, EVENTOUT	ADC3_IN5
-	-	-	20	26	L3	PF8	I/O	FT	(4)	TIM13_CH1, FSMC_NIOWR, EVENTOUT	ADC3_IN6
-	-	-	21	27	L2	PF9	I/O	FT	(4)	TIM14_CH1, FSMC_CD, EVENTOUT	ADC3_IN7
-	-	-	22	28	L1	PF10	I/O	FT	(4)	FSMC_INTR, EVENTOUT	ADC3_IN8
5	E9	12	23	29	G1	PH0/OSC_IN (PH0)	I/O	FT	-	EVENTOUT	OSC_IN(4)
6	F9	13	24	30	H1	PH1/OSC_OUT (PH1)	I/O	FT	-	EVENTOUT	OSC_OUT(4)
7	E8	14	25	31	J1	NRST	I/O		-	-	-
8	G9	15	26	32	M2	PC0	I/O	FT	(4)	OTG_HS_ULPI_STP, EVENTOUT	ADC123_ IN10
9	F8	16	27	33	M3	PC1	I/O	FT	(4)	ETH_MDC, EVENTOUT	ADC123_ IN11
10	D7	17	28	34	M4	PC2	I/O	FT	(4)	SPI2_MISO, OTG_HS_ULPI_DIR, ETH_MII_TXD2, EVENTOUT	ADC123_ IN12
11	G8	18	29	35	M5	PC3	I/O	FT	(4)	SPI2_MOSI, I2S2_SD, OTG_HS_ULPI_NXT, ETH_MII_TX_CLK, EVENTOUT	ADC123_ IN13
-	-	19	30	36	-	V_{DD}	S	-	-	-	-
12	-	20	31	37	M1	V_{SSA}	S	-	-	-	-
-	-	-	-	-	N1	V_{REF-}	S	-	-	-	-
-	F7	21	32	38	P1	V_{REF+}	S	-	-	-	-

Table 8. STM32F20x pin and ball definitions (continued)

Pins						Pin name (function after reset)[1]	Pin type	I/O structure	Note	Alternate functions	Additional functions
LQFP64	WLCSP64+2	LQFP100	LQFP144	LQFP176	UFBGA176						
54	C7	83	116	144	D12	PD2	I/O	FT	-	TIM3_ETR,UART5_RX, SDIO_CMD, DCMI_D11, EVENTOUT	-
-	-	84	117	145	D11	PD3	I/O	FT	-	FSMC_CLK,USART2_CTS, EVENTOUT	-
-	-	85	118	146	D10	PD4	I/O	FT	-	FSMC_NOE, USART2_RTS, EVENTOUT	-
-	-	86	119	147	C11	PD5	I/O	FT	-	FSMC_NWE,USART2_TX, EVENTOUT	-
-	-	-	120	148	D8	V_{SS}	S	-	-	-	-
-	-	-	121	149	C8	V_{DD}	S	-	-	-	-
-	-	87	122	150	B11	PD6	I/O	FT	-	FSMC_NWAIT, USART2_RX, EVENTOUT	-
-	-	88	123	151	A11	PD7	I/O	FT	-	USART2_CK,FSMC_NE1, FSMC_NCE2, EVENTOUT	-
-	-	-	124	152	C10	PG9	I/O	FT	-	USART6_RX, FSMC_NE2,FSMC_NCE3, EVENTOUT	-
-	-	-	125	153	B10	PG10	I/O	FT	-	FSMC_NCE4_1, FSMC_NE3, EVENTOUT	-
-	-	-	126	154	B9	PG11	I/O	FT	-	FSMC_NCE4_2, ETH_MII_TX_EN , ETH _RMII_TX_EN, EVENTOUT	-
-	-	-	127	155	B8	PG12	I/O	FT	-	FSMC_NE4, USART6_RTS, EVENTOUT	-
-	-	-	128	156	A8	PG13	I/O	FT	-	FSMC_A24, USART6_CTS, ETH_MII_TXD0, ETH_RMII_TXD0, EVENTOUT	-
-	-	-	129	157	A7	PG14	I/O	FT	-	FSMC_A25, USART6_TX, ETH_MII_TXD1, ETH_RMII_TXD1, EVENTOUT	-
-	-	-	130	158	D7	V_{SS}	S	-	-	-	-

Table 8. STM32F20x pin and ball definitions (continued)

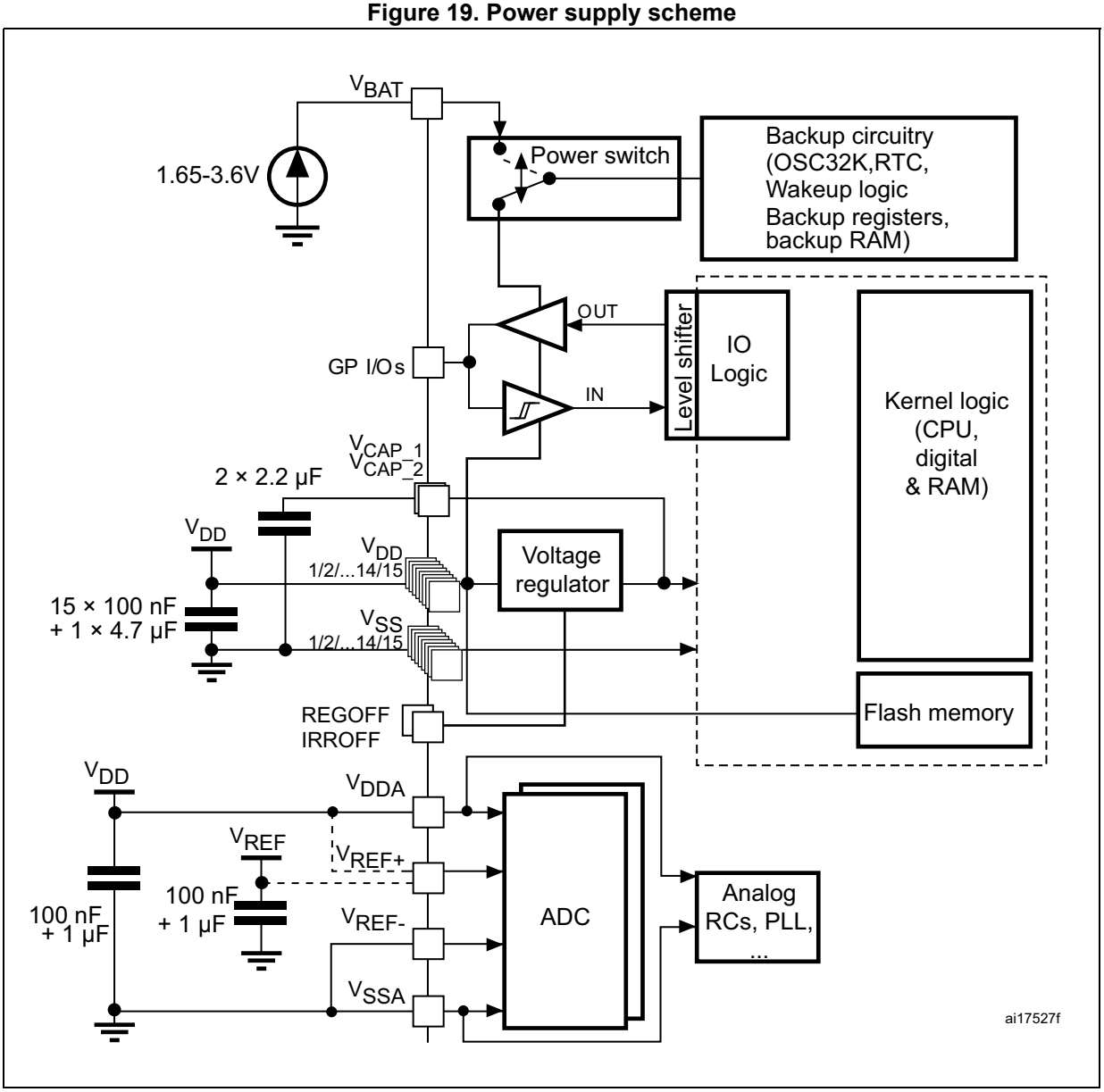
Pins						Pin name (function after reset)(1)	Pin type	I/O structure	Note	Alternate functions	Additional functions
LQFP64	WLCSP64+2	LQFP100	LQFP144	LQFP176	UFBGA176						
-	-	-	131	159	C7	V_{DD}	S	-	-	-	-
-	-	-	132	160	B7	PG15	I/O	FT	-	USART6_CTS, DCMI_D13, EVENTOUT	-
55	A4	89	133	161	A10	PB3 (JTDO/TRACESWO)	I/O	FT	-	JTDO/ TRACESWO, SPI3_SCK, I2S3_SCK, TIM2_CH2, SPI1_SCK, EVENTOUT	-
56	B4	90	134	162	A9	PB4	I/O	FT	-	NJTRST, SPI3_MISO, TIM3_CH1, SPI1_MISO, EVENTOUT	-
57	A5	91	135	163	A6	PB5	I/O	FT	-	I2C1_SMBA, CAN2_RX, OTG_HS_ULPI_D7, ETH_PPS_OUT, TIM3_CH2, SPI1_MOSI, SPI3_MOSI, DCMI_D10, I2S3_SD, EVENTOUT	-
58	B5	92	136	164	B6	PB6	I/O	FT	-	I2C1_SCL,, TIM4_CH1, CAN2_TX, DCMI_D5,USART1_TX, EVENTOUT	-
59	A6	93	137	165	B5	PB7	I/O	FT	-	I2C1_SDA, FSMC_NL(6), DCMI_VSYNC, USART1_RX, TIM4_CH2, EVENTOUT	-
60	B6	94	138	166	D6	BOOT0	I	B	-	-	V_{PP}
61	B7	95	139	167	A5	PB8	I/O	FT	-	TIM4_CH3,SDIO_D4, TIM10_CH1, DCMI_D6, ETH_MII_TXD3, I2C1_SCL, CAN1_RX, EVENTOUT	-
62	A7	96	140	168	B4	PB9	I/O	FT	-	SPI2_NSS, I2S2_WS, TIM4_CH4, TIM11_CH1, SDIO_D5, DCMI_D7, I2C1_SDA, CAN1_TX, EVENTOUT	-
-	-	97	141	169	A4	PE0	I/O	FT	-	TIM4_ETR, FSMC_NBL0, DCMI_D2, EVENTOUT	-

Table 10. Alternate function mapping

Port		AF0	AF1	AF2	AF3	AF4	AF5	AF6	AF7	AF8	AF9	AF10	AF11	AF12	AF13	AF014	AF15
		SYS	TIM1/2	TIM3/4/5	TIM8/9/10/11	I2C1/I2C2/I2C3	SPI1/SPI2/I2S2	SPI3/I2S3	USART1/2/3	UART4/5/ USART6	CAN1/CAN2/ TIM12/13/14	OTG_FS/ OTG_HS	ETH	FSMC/SDIO/ OTG_HS	DCMI		
Port A	PA0-WKUP	-	TIM2_CH1_ETR	TIM 5_CH1	TIM8_ETR	-	-		USART2_CTS	UART4_TX	-	-	ETH_MII_CRS	-	-	-	EVENTOUT
	PA1	-	TIM2_CH2	TIM5_CH2	-	-	-		USART2_RTS	UART4_RX	-	-	ETH_MII _RX_CLK ETH_RMII _REF_CLK	-	-	-	EVENTOUT
	PA2	-	TIM2_CH3	TIM5_CH3	TIM9_CH1	-	-		USART2_TX	-	-	-	ETH_MDIO	-	-	-	EVENTOUT
	PA3	-	TIM2_CH4	TIM5_CH4	TIM9_CH2	-	-		USART2_RX	-	-	OTG_HS_ULPI_D0	ETH _MII_COL	-	-	-	EVENTOUT
	PA4	-	-	-	-	-	SPI1_NSS	SPI3_NSS I2S3_WS	USART2_CK	-	-		-	OTG_HS_SOF	DCMI_HSYNC	-	EVENTOUT
	PA5	-	TIM2_CH1_ETR	-	TIM8_CH1N	-	SPI1_SCK	-	-	-	-	OTG_HS_ULPI_C K	-	-	-	-	EVENTOUT
	PA6	-	TIM1_BKIN	TIM3_CH1	TIM8_BKIN	-	SPI1_MISO	-	-	-	TIM13_CH1	-	-	-	DCMI_PIXCK	-	EVENTOUT
	PA7	-	TIM1_CH1N	TIM3_CH2	TIM8_CH1N	-	SPI1_MOSI	-	-	-	TIM14_CH1	-	ETH_MII _RX_DV ETH_RMII _CRS_DV	-	-	-	EVENTOUT
	PA8	MCO1	TIM1_CH1	-	-	I2C3_SCL	-	-	USART1_CK	-	-	OTG_FS_SOF	-	-	-	-	EVENTOUT
	PA9	-	TIM1_CH2	-	-	I2C3_SMBA	-	-	USART1_TX	-	-		-	-	DCMI_D0	-	EVENTOUT
	PA10	-	TIM1_CH3	-	-	-	-	-	USART1_RX	-	-	OTG_FS_ID	-	-	DCMI_D1	-	EVENTOUT
	PA11	-	TIM1_CH4	-	-	-	-	-	USART1_CTS	-	CAN1_RX	OTG_FS_DM	-	-	-	-	EVENTOUT
	PA12	-	TIM1_ETR	-	-	-	-	-	USART1_RTS	-	CAN1_TX	OTG_FS_DP	-	-	-	-	EVENTOUT
	PA13	JTMS-SWDIO	-	-	-	-	-	-	-	-	-	-	-	-	-	-	EVENTOUT
	PA14	JTCK-SWCLK	-	-	-	-	-	-	-	-	-	-	-	-	-	-	EVENTOUT
	PA15	JTDI	TIM 2_CH1 TIM 2_ETR	-	-	-	SPI1_NSS	SPI3_NSS I2S3_WS	-	-	-	-	-	-	-	-	EVENTOUT

6.1.6 Power supply scheme

Figure 19. Power supply scheme



1. Each power supply pair must be decoupled with filtering ceramic capacitors as shown above. These capacitors must be placed as close as possible to, or below, the appropriate pins on the underside of the PCB to ensure the good functionality of the device.
2. To connect REGOFF and IRROFF pins, refer to *Section 3.16: Voltage regulator*.
3. The two 2.2 µF ceramic capacitors should be replaced by two 100 nF decoupling capacitors when the voltage regulator is OFF.
4. The 4.7 µF ceramic capacitor must be connected to one of the V_{DD} pin.

Caution: Each power supply pair (V_{DD}/V_{SS}, V_{DDA}/V_{SSA} ...) must be decoupled with filtering ceramic capacitors as shown above. These capacitors must be placed as close as possible to, or below, the appropriate pins on the underside of the PCB, to ensure good device operation. It is not recommended to remove filtering capacitors to reduce PCB size or cost. This might cause incorrect device operation.

Table 12. Current characteristics

Symbol	Ratings	Max.	Unit
I_{VDD}	Total current into V_{DD} power lines (source)(1)	120	mA
I_{VSS}	Total current out of V_{SS} ground lines (sink)(1)	120	
I_{IO}	Output current sunk by any I/O and control pin	25	
	Output current source by any I/Os and control pin	25	
$I_{INJ(PIN)}$ (2)	Injected current on five-volt tolerant I/O(3)	–5/+0	
	Injected current on any other pin(4)	±5	
$\Sigma I_{INJ(PIN)}$(4)	Total injected current (sum of all I/O and control pins)(5)	±25	

1. All main power (V_{DD}, V_{DDA}) and ground (V_{SS}, V_{SSA}) pins must always be connected to the external power supply, in the permitted range.
2. Negative injection disturbs the analog performance of the device. See note in *Section 6.3.20: 12-bit ADC characteristics*.
3. Positive injection is not possible on these I/Os. A negative injection is induced by $V_{IN}<V_{SS}$. $I_{INJ(PIN)}$ must never be exceeded. Refer to *Table 11* for the values of the maximum allowed input voltage.
4. A positive injection is induced by $V_{IN}>V_{DD}$ while a negative injection is induced by $V_{IN}<V_{SS}$. $I_{INJ(PIN)}$ must never be exceeded. Refer to *Table 11* for the values of the maximum allowed input voltage.
5. When several inputs are submitted to a current injection, the maximum $\Sigma I_{INJ(PIN)}$ is the absolute sum of the positive and negative injected currents (instantaneous values).

Table 13. Thermal characteristics

Symbol	Ratings	Value	Unit
T_{STG}	Storage temperature range	–65 to +150	°C
T_J	Maximum junction temperature	125	°C

6.3 Operating conditions

6.3.1 General operating conditions

Table 14. General operating conditions

Symbol	Parameter	Conditions	Min	Max	Unit
f_{HCLK}	Internal AHB clock frequency	-	0	120	MHz
f_{PCLK1}	Internal APB1 clock frequency	-	0	30	
f_{PCLK2}	Internal APB2 clock frequency	-	0	60	

Table 37. Flash memory characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
I_{DD}	Supply current	Write / Erase 8-bit mode V_{DD} = 1.8 V	-	5	-	mA
		Write / Erase 16-bit mode V_{DD} = 2.1 V	-	8	-	
		Write / Erase 32-bit mode V_{DD} = 3.3 V	-	12	-	

Table 38. Flash memory programming

Symbol	Parameter	Conditions	Min(1)	Typ	Max(1)	Unit
t_{prog}	Word programming time	Program/erase parallelism (PSIZE) = x 8/16/32	-	16	100(2)	µs
$t_{ERASE16KB}$	Sector (16 KB) erase time	Program/erase parallelism (PSIZE) = x 8	-	400	800	ms
		Program/erase parallelism (PSIZE) = x 16	-	300	600	
		Program/erase parallelism (PSIZE) = x 32	-	250	500	
$t_{ERASE64KB}$	Sector (64 KB) erase time	Program/erase parallelism (PSIZE) = x 8	-	1200	2400	ms
		Program/erase parallelism (PSIZE) = x 16	-	700	1400	
		Program/erase parallelism (PSIZE) = x 32	-	550	1100	
$t_{ERASE128KB}$	Sector (128 KB) erase time	Program/erase parallelism (PSIZE) = x 8	-	2	4	s
		Program/erase parallelism (PSIZE) = x 16	-	1.3	2.6	
		Program/erase parallelism (PSIZE) = x 32	-	1	2	
t_{ME}	Mass erase time	Program/erase parallelism (PSIZE) = x 8	-	16	32	s
		Program/erase parallelism (PSIZE) = x 16	-	11	22	
		Program/erase parallelism (PSIZE) = x 32	-	8	16	
V_{prog}	Programming voltage	32-bit program operation	2.7	-	3.6	V
		16-bit program operation	2.1	-	3.6	V
		8-bit program operation	1.8	-	3.6	V

1. Guaranteed by characterization results, not tested in production.
2. The maximum programming time is measured after 100K erase operations.

6.3.16 I/O port characteristics

General input/output characteristics

Unless otherwise specified, the parameters given in *Table 50* are derived from tests performed under the conditions summarized in *Table 14: General operating conditions*.

All I/Os are CMOS and TTL compliant.

Table 46. I/O static characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{IL}	FT, TTa and NRST I/O input low level voltage	1.7 V≤V_{DD}≤3.6 V	-	-	$0.35V_{DD}-0.04^{(1)}$ $0.3V_{DD}^{(2)}$	V
	BOOT0 I/O input low level voltage	1.75 V≤V_{DD} ≤3.6 V, –40 °C≤T_A ≤105 °C	-	-	$0.1V_{DD}+0.1^{(1)}$	
		1.7 V≤V_{DD} ≤3.6 V, 0 °C≤T_A ≤105 °C	-	-		
V_{IH}	FT, TTa and NRST I/O input high level voltage(5)	1.7 V≤V_{DD}≤3.6 V	$0.45V_{DD}+0.3^{(1)}$ $0.7V_{DD}^{(2)}$	-	-	V
	BOOT0 I/O input high level voltage	1.75 V≤V_{DD} ≤3.6 V, –40 °C≤T_A ≤105 °C	$0.17V_{DD}+0.7^{(1)}$	-	-	
		1.7 V≤V_{DD} ≤3.6 V, 0 °C≤T_A ≤105 °C				
V_{HYS}	FT, TTa and NRST I/O input hysteresis	1.7 V≤V_{DD}≤3.6 V	$0.45V_{DD}+0.3^{(1)}$	-	-	V
	BOOT0 I/O input hysteresis	1.75 V≤V_{DD} ≤3.6 V, –40 °C≤T_A ≤105 °C	$10\%V_{DDIO}^{(1)(3)}$	-	-	
		1.7 V≤V_{DD} ≤3.6 V, 0 °C≤T_A ≤105 °C	$100^{(1)}$	-	-	
I_{lkg}	I/O input leakage current (4)	V_{SS} ≤V_{IN} ≤V_{DD}	-	-	±1	µA
	I/O FT input leakage current (5)	V_{IN} = 5 V	-	-	3	

6.3.18 TIM timer characteristics

The parameters given in *Table 50* and *Table 51* are guaranteed by design.

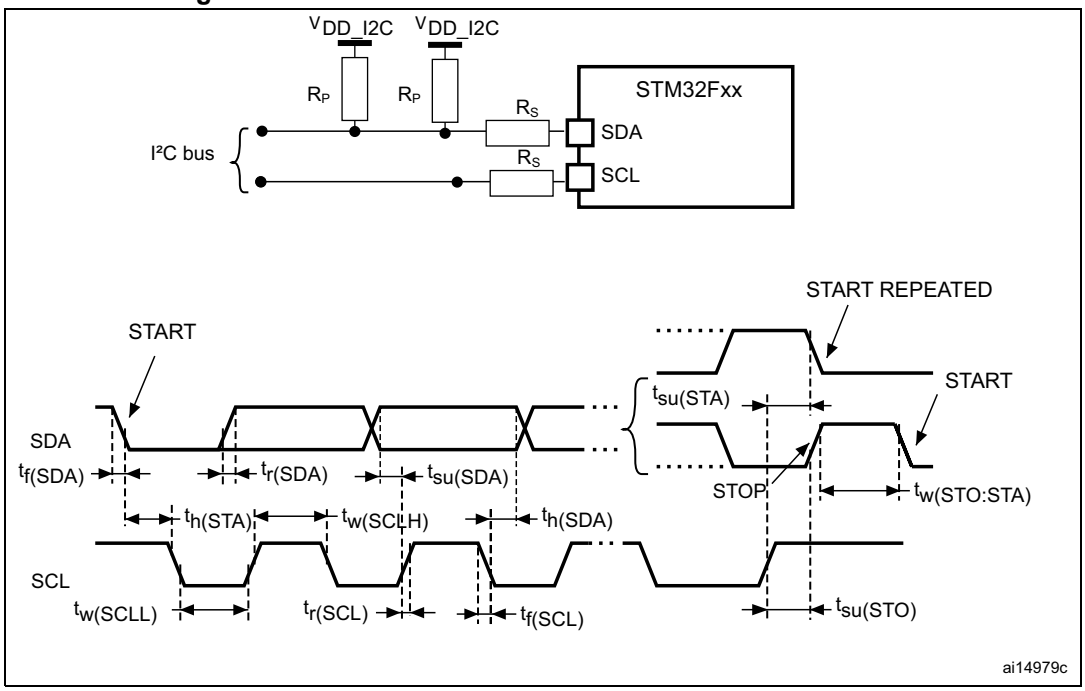
Refer to *Section 6.3.16: I/O port characteristics* for details on the input/output alternate function characteristics (output compare, input capture, external clock, PWM output).

Table 50. Characteristics of TIMx connected to the APB1 domain(1)

Symbol	Parameter	Conditions	Min	Max	Unit
$t_{res(TIM)}$	Timer resolution time	AHB/APB1 prescaler distinct from 1, $f_{TIMxCLK}$ = 60 MHz	1	-	$t_{TIMxCLK}$
			16.7	-	ns
		AHB/APB1 prescaler = 1, $f_{TIMxCLK}$ = 30 MHz	1	-	$t_{TIMxCLK}$
			33.3	-	ns
f_{EXT}	Timer external clock frequency on CH1 to CH4	$f_{TIMxCLK}$ = 60 MHz APB1= 30 MHz	0	$f_{TIMxCLK}/2$	MHz
			0	30	MHz
Res_{TIM}	Timer resolution		-	16/32	bit
$t_{COUNTER}$	16-bit counter clock period when internal clock is selected		1	65536	$t_{TIMxCLK}$
			0.0167	1092	µs
	32-bit counter clock period when internal clock is selected		1	-	$t_{TIMxCLK}$
			0.0167	71582788	µs
t_{MAX_COUNT}	Maximum possible count		-	65536 × 65536	$t_{TIMxCLK}$
			-	71.6	s

1. TIMx is used as a general term to refer to the TIM2, TIM3, TIM4, TIM5, TIM6, TIM7, and TIM12 timers.

Figure 41. I²C bus AC waveforms and measurement circuit



1. R_S= series protection resistor.
2. R_P = external pull-up resistor.
3. V_{DD_I2C} is the I²C bus power supply.

Table 53. SCL frequency (f_{PCLK1}= 30 MHz.,V_{DD} = 3.3 V)(1)(2)

f_{SCL} (kHz)	I2C_CCR value
	R_P = 4.7 kΩ
400	0x8019
300	0x8021
200	0x8032
100	0x0096
50	0x012C
20	0x02EE

1. R_P = External pull-up resistance, f_{SCL} = I²C speed,
2. For speeds around 200 kHz, the tolerance on the achieved speed is of ±5%. For other speed ranges, the tolerance on the achieved speed ±2%. These variations depend on the accuracy of the external components used to design the application.

Figure 42. SPI timing diagram - slave mode and CPHA = 0

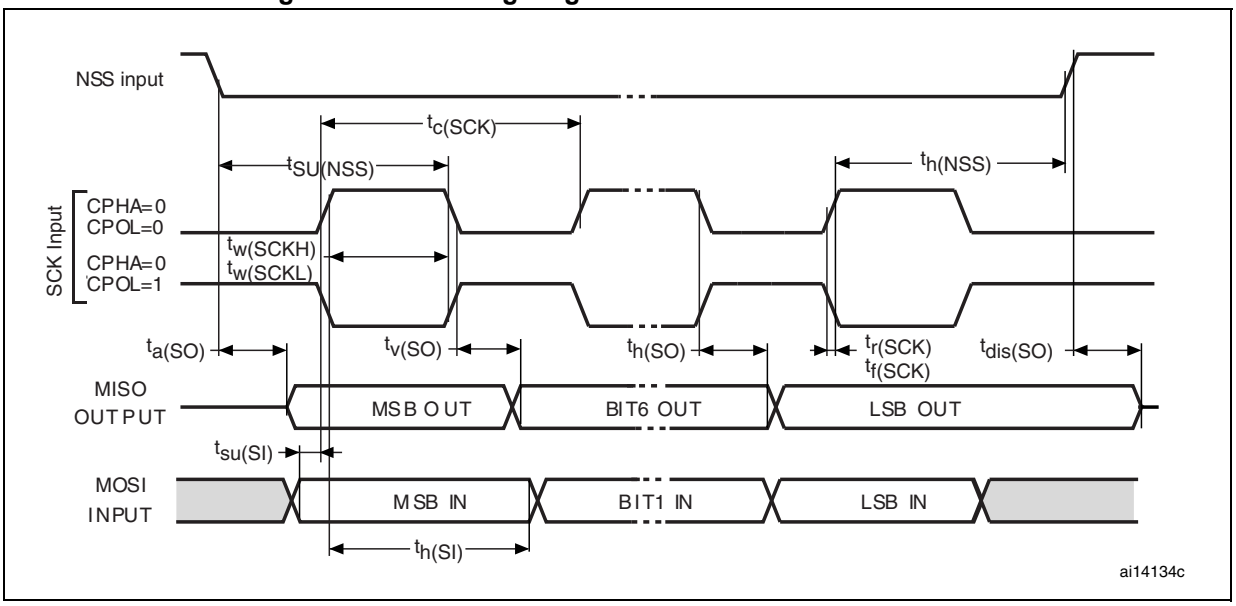
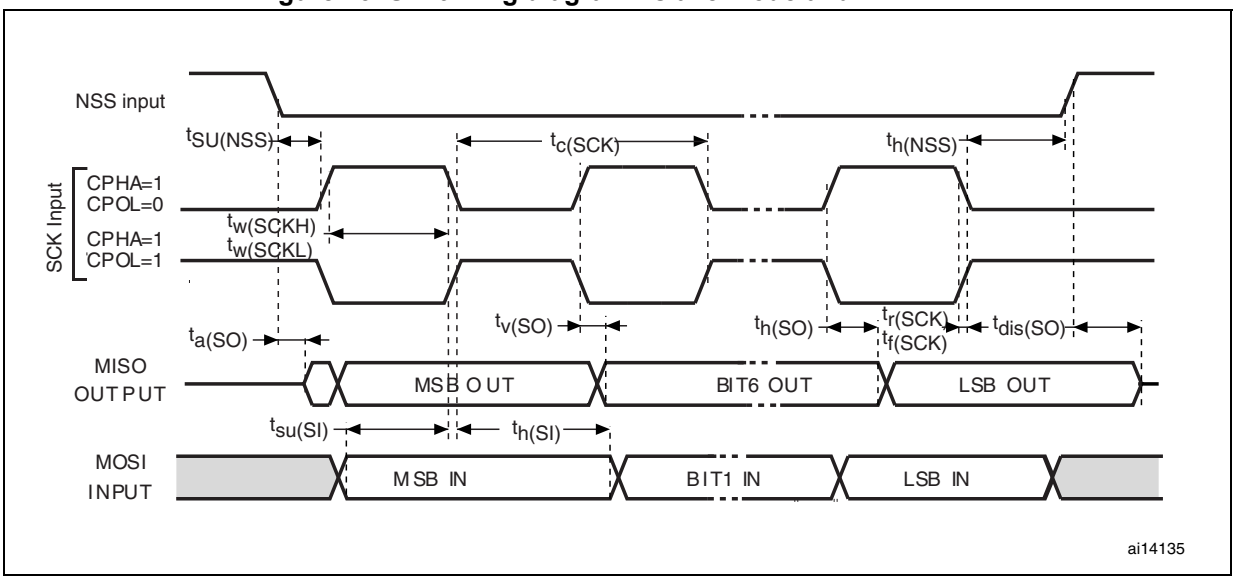


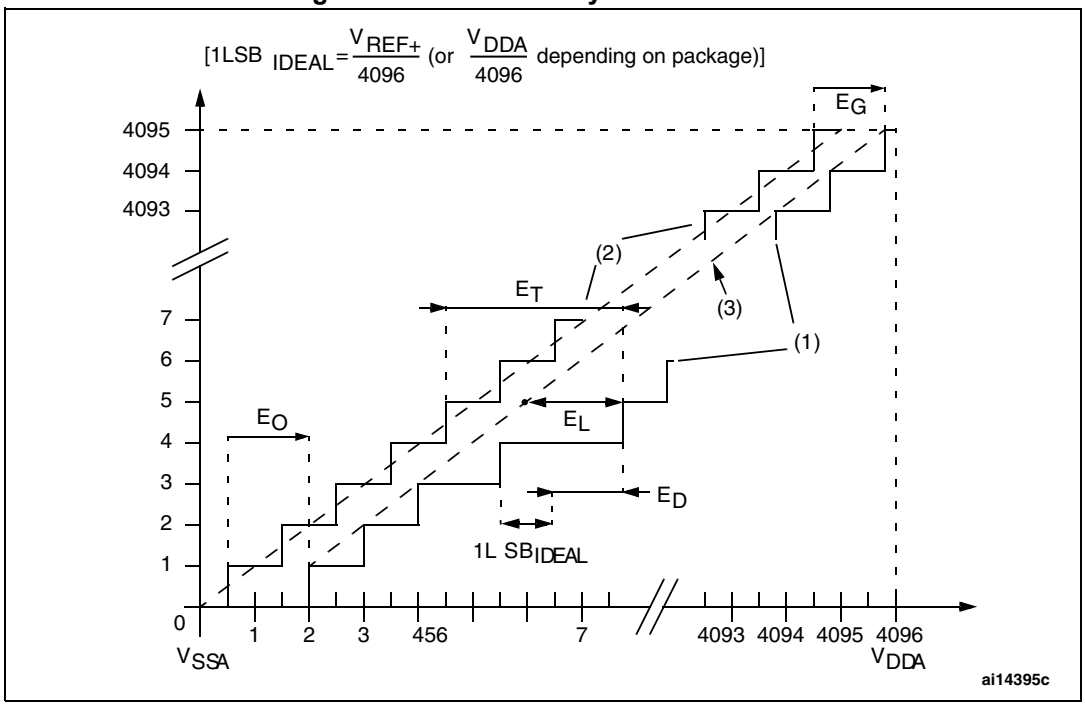
Figure 43. SPI timing diagram - slave mode and CPHA = 1



being performed on another analog input. It is recommended to add a Schottky diode (pin to ground) to analog pins which may potentially inject negative currents.

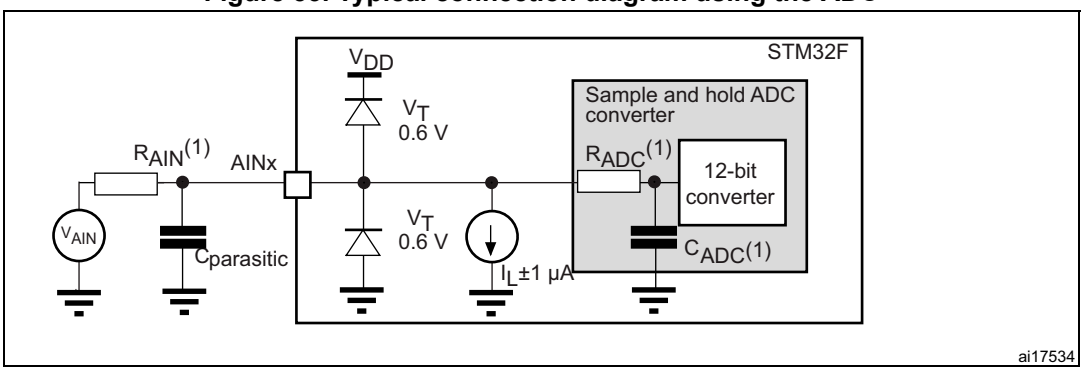
Any positive injection current within the limits specified for $I_{INJ(PIN)}$ and $\Sigma I_{INJ(PIN)}$ in *Section 6.3.16* does not affect the ADC accuracy.

Figure 52. ADC accuracy characteristics



1. Example of an actual transfer curve.
2. Ideal transfer curve.
3. End point correlation line.
4. E_T = Total Unadjusted Error: maximum deviation between the actual and the ideal transfer curves.
   EO = Offset Error: deviation between the first actual transition and the first ideal one.
   EG = Gain Error: deviation between the last ideal transition and the last actual one.
   ED = Differential Linearity Error: maximum deviation between actual steps and the ideal one.
   EL = Integral Linearity Error: maximum deviation between any actual transition and the end point correlation line.

Figure 53. Typical connection diagram using the ADC



1. Refer to *Table 66* for the values of R_{AIN}, R_{ADC} and C_{ADC}.
2. $C_{parasitic}$ represents the capacitance of the PCB (dependent on soldering and PCB layout quality) plus the pad capacitance (roughly 7 pF). A high $C_{parasitic}$ value downgrades conversion accuracy. To remedy this, f_{ADC} should be reduced.

Table 83. Switching characteristics for NAND Flash write cycles(1)(2)

Symbol	Parameter	Min	Max	Unit
$t_{w(NWE)}$	FSMC_NWE low width	$4T_{HCLK}$- 1	$4T_{HCLK}$+ 3	ns
$t_{v(NWE-D)}$	FSMC_NWE low to FSMC_D[15-0] valid	-	0	ns
$t_{h(NWE-D)}$	FSMC_NWE high to FSMC_D[15-0] invalid	$3T_{HCLK}$	-	ns
$t_{d(D-NWE)}$	FSMC_D[15-0] valid before FSMC_NWE high	$5T_{HCLK}$	-	ns
$t_{d(ALE-NWE)}$	FSMC_ALE valid before FSMC_NWE low	-	$3T_{HCLK}$+ 2	ns
$t_{h(NWE-ALE)}$	FSMC_NWE high to FSMC_ALE invalid	$3T_{HCLK}$- 2	-	ns

1. C_L = 30 pF.
2. Guaranteed by characterization results, not tested in production.

6.3.26 Camera interface (DCMI) timing specifications

Table 84. DCMI characteristics

Symbol	Parameter	Conditions	Min	Max
-	Frequency ratio DCMI_PIXCLK/f_{HCLK}	DCMI_PIXCLK= 48 MHz	-	0.4

6.3.27 SD/SDIO MMC card host interface (SDIO) characteristics

Unless otherwise specified, the parameters given in *Table 85* are derived from tests performed under ambient temperature, f_{PCLKx} frequency and V_{DD} supply voltage conditions summarized in *Table 14*.

Refer to *Section 6.3.16: I/O port characteristics* for more details on the input/output alternate function characteristics (D[7:0], CMD, CK).

Figure 75. SDIO high-speed mode

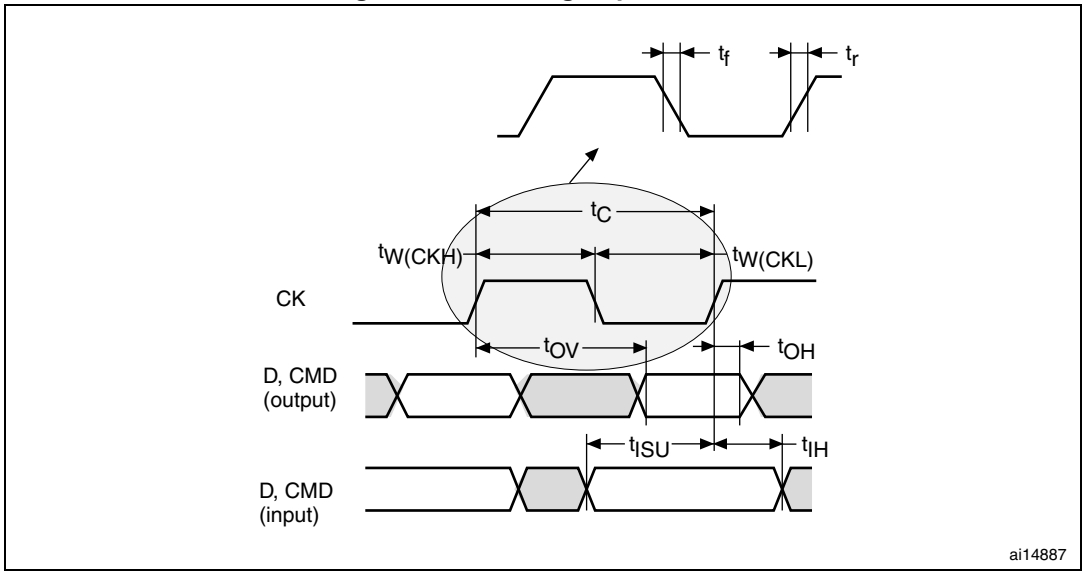
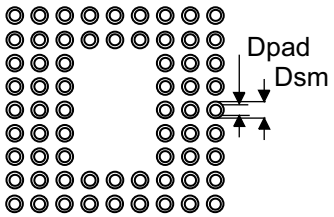


Table 88. WLCSP64+2 - 66-ball, 4.539 x 4.911 mm, 0.4 mm pitch wafer level chip scale package mechanical data (continued)

Symbol	millimeters			inches[1]		
	Min	Typ	Max	Min	Typ	Max
F	-	0.220	-	-	0.0087	-
G	-	0.386	-	-	0.0152	-
aaa	-	-	0.100	-	-	0.0039
bbb	-	-	0.100	-	-	0.0039
ccc	-	-	0.100	-	-	0.0039
ddd	-	-	0.050	-	-	0.0020
eee	-	-	0.050	-	-	0.0020

1. Values in inches are converted from mm and rounded to 4 decimal digits.
2. Dimension is measured at the maximum bump diameter parallel to primary datum Z.

Figure 80. WLCSP64+2 - 66-ball, 4.539 x 4.911 mm, 0.4 mm pitch wafer level chip scale package recommended footprint



A0FX_FP_V1

Table 89. WLCSP64 recommended PCB design rules (0.4 mm pitch)

Dimension	Recommended values
Pitch	0.4
Dpad	0.225 mm
Dsm	0.290 mm typ. (depends on the soldermask registration tolerance)
Stencil opening	0.250 mm
Stencil thickness	0.100 mm

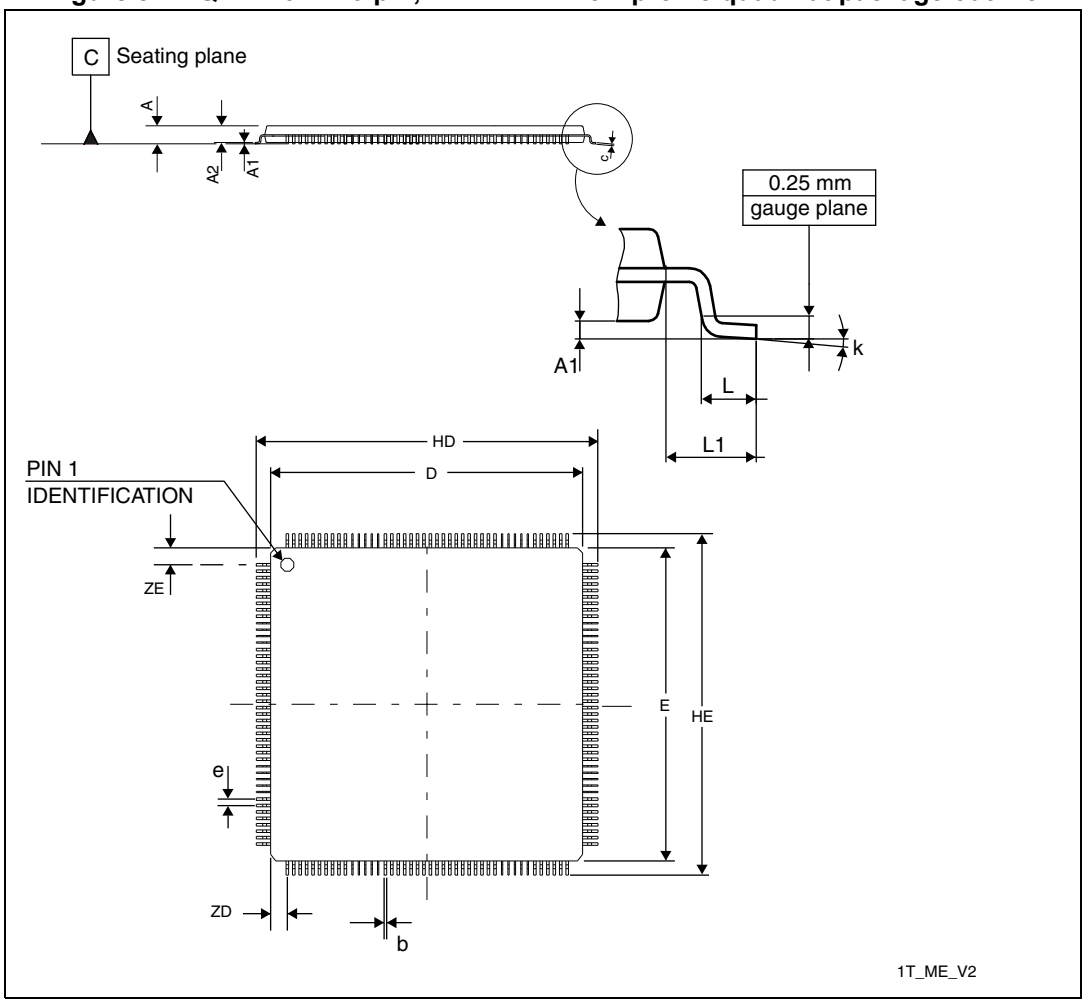
Table 91. LQFP144 - 144-pin, 20 x 20 mm low-profile quad flat package mechanical data

Symbol	millimeters			inches[1]		
	Min	Typ	Max	Min	Typ	Max
A	-	-	1.600	-	-	0.0630
A1	0.050	-	0.150	0.0020	-	0.0059
A2	1.350	1.400	1.450	0.0531	0.0551	0.0571
b	0.170	0.220	0.270	0.0067	0.0087	0.0106
c	0.090	-	0.200	0.0035	-	0.0079
D	21.800	22.000	22.200	0.8583	0.8661	0.8740
D1	19.800	20.000	20.200	0.7795	0.7874	0.7953
D3	-	17.500	-	-	0.6890	-
E	21.800	22.000	22.200	0.8583	0.8661	0.8740
E1	19.800	20.000	20.200	0.7795	0.7874	0.7953
E3	-	17.500	-	-	0.6890	-
e	-	0.500	-	-	0.0197	-
L	0.450	0.600	0.750	0.0177	0.0236	0.0295
L1	-	1.000	-	-	0.0394	-
k	0°	3.5°	7°	0°	3.5°	7°
ccc	-	-	0.080	-	-	0.0031

1. Values in inches are converted from mm and rounded to 4 decimal digits.

7.5 LQFP176 package information

Figure 87. LQFP176 - 176-pin, 24 x 24 mm low profile quad flat package outline



1. Drawing is not to scale.

Table 92. LQFP176 - 176-pin, 24 x 24 mm low profile quad flat package mechanical data

Symbol	Dimensions					
	millimeters			inches[1]		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	-	-	1.600	-	-	0.0630
A1	0.050	-	0.150	0.0020	-	0.0059
A2	1.350	-	1.450	0.0531	-	0.0571
b	0.170	-	0.270	0.0067	-	0.0106
c	0.090	-	0.200	0.0035	-	0.0079
D	23.900	-	24.100	0.9409	-	0.9488

Table 97. Document revision history (continued)

Date	Revision	Changes
13-Jul-2010	4 (continued)	Added USB OTG_FS features in *Section 3.28: Universal serial bus on-the-go full-speed (OTG_FS)*. Updated V_{CAP_1} and V_{CAP_2} capacitor value to 2.2 µF in *Figure 19: Power supply scheme*. Removed DAC, modified ADC limitations, and updated I/O compensation for 1.8 to 2.1 V range in *Table 15: Limitations depending on the operating power supply range*. Added V_{BORL}, V_{BORM}, V_{BORH} and I_{RUSH} in *Table 19: Embedded reset and power control block characteristics*. Removed table Typical current consumption in Sleep mode with Flash memory in Deep power down mode. Merged typical and maximum current consumption sections and added *Table 21: Typical and maximum current consumption in Run mode, code with data processing running from Flash memory (ART accelerator disabled)*, *Table 20: Typical and maximum current consumption in Run mode, code with data processing running from Flash memory (ART accelerator enabled) or RAM, Table 22: Typical and maximum current consumption in Sleep mode, Table 23: Typical and maximum current consumptions in Stop mode, Table 24: Typical and maximum current consumptions in Standby mode*, and *Table 25: Typical and maximum current consumptions in VBAT mode*. Update *Table 34: Main PLL characteristics* and added *Section 6.3.11: PLL spread spectrum clock generation (SSCG) characteristics*. Added *Note 8* for CIO in *Table 48: I/O AC characteristics*. Updated *Section 6.3.18: TIM timer characteristics*. Added T_{NRST_OUT} in *Table 49: NRST pin characteristics*. Updated *Table 52: I2C characteristics*. Removed 8-bit data in and data out waveforms from *Figure 48: ULPI timing diagram*. Removed note related to ADC calibration in *Table 67*. *Section 6.3.20: 12-bit ADC characteristics*: ADC characteristics tables merged into one single table; tables ADC conversion time and ADC accuracy removed. Updated *Table 68: DAC characteristics*. Updated *Section 6.3.22: Temperature sensor characteristics* and *Section 6.3.23: VBAT monitoring characteristics*. Update *Section 6.3.26: Camera interface (DCMI) timing specifications*. Added *Section 6.3.27: SD/SDIO MMC card host interface (SDIO) characteristics*, and *Section 6.3.28: RTC characteristics*. Added *Section 7.7: Thermal characteristics*. Updated *Table 91: LQFP176 - Low profile quad flat package 24 × 24 × 1.4 mm package mechanical data* and *Figure 86: LQFP176 - Low profile quad flat package 24 × 24 × 1.4 mm, package outline*. Changed tape and reel code to TX in *Table 96: Ordering information scheme*. Added *Table 101: Main applications versus package for STM32F2xxx microcontrollers*. Updated figures in Appendix *A.2: USB OTG full speed (FS) interface solutions* and *A.3: USB OTG high speed (HS) interface solutions*. Updated *Figure 94: Audio player solution using PLL, PLLI2S, USB and 1 crystal* and *Figure 95: Audio PLL (PLLI2S) providing accurate I2S clock*.